SHI LING® 浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

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Specifcation of products

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„ ن گ: MURP600600CT

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Ultra-Fast Soft Recovery Diode Module

MURP600600CT

Description

Ultra-FRD module devices are optimized to reduce losses and EMI/RFI in high frequency power conditioning electrical systems. These diode modules are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

Features

- ☞ Repetitive Reverse Voltage : V_{RRM} =600V
- ☞ Low Forward Voltage Drop : V_F (typ.) = 1.5V
- ☞ Average Forward Current : I_F (AV.) = 300A @ Tc= 100 ℃
- ☞ Ultra-Fast Reverse Recovery Time : t_{rr} (typ.) = 100 ns
- ☞ Extensive Characterization of Recovery Parameters
- ☞ Reduced EMI and RFI
- ☞ Non Isolation Type Package

Applications

Motor Drives, Free wheel use, High Power Converters, Welders, Various Switching and Telecommunication Power Supply.

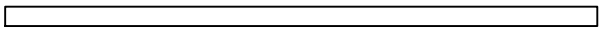
Absolute Maximum Ratings @ T_j =2

Thermal Characteristics

Symbol	Parameter	Conditions	Values			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)}$	Thermal Resistance	Junction to Case	-	-	0.10	℃/W

Electrical Characteristics @ T_j=25℃ (unless otherwise specified)

Symbol	Parameter	Conditions		Values			Unit
				Min.	Typ.	Max.	
V_R	Cathode Anode Breakdown Voltage	I_R = 100uA		600	–	–	V
V_{FM}	Maximum Forward Voltage	I_{FM}= 300A, T_c = 25℃		–	1.5	1.6	V
		I_{FM}= 300A, T_c =100℃		–	1.3	1.5	V
I_{RRM}	Repetitive Peak Reverse Current	T_C = 100℃, V_{RRM} applied		–	–	3.0	mA
t_{rr}	Reverse Recovery Time	I_{FM}= 300A, V_R= 150V di/dt=-100A/us	T_C = 25℃	–	100	110	ns
			T_C = 100℃	–	180	–	ns



Performance Curves

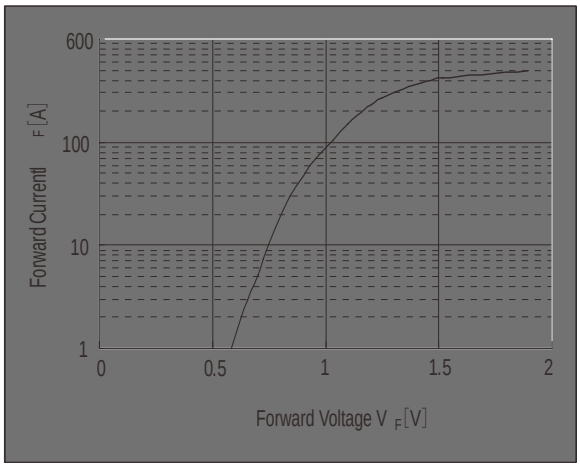


Fig. 1 : Typical Forward Voltage Drop vs. Instantaneous Forward Current

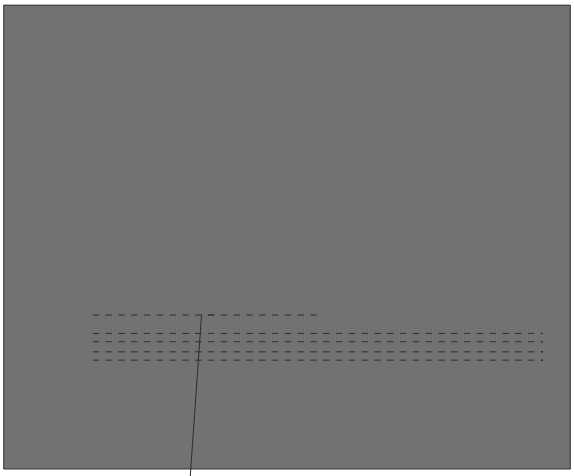


Fig. 2 : Typical Reverse Recovery Time vs. -di/dt